

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
20V	24mΩ @ V <sub>GS</sub> = 4.5V	6.2A
	28mΩ @ V <sub>GS</sub> = 2.5V	5.7A

## Description and Applications

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

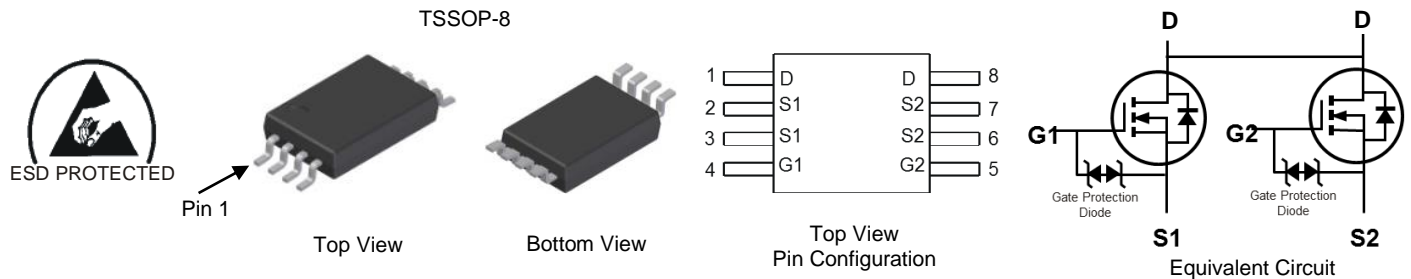
- Battery Management Application
- Power Management Functions
- DC-DC Converters

## Features and Benefits

- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](https://www.diodes.com/quality/product-definitions/) or your local Diodes representative.

## Mechanical Data

- Case: TSSOP-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Weight: 0.039 grams (Approximate)

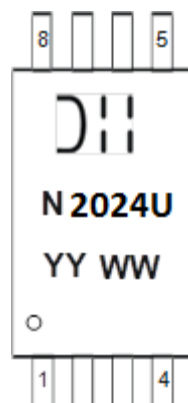


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2024UTS-13	TSSOP-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



D ::= Manufacturer's Marking  
 N2024U = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 20 = 2020)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±10	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	6.2 4.9	A
	Steady State	T <sub>C</sub> = +25°C T <sub>C</sub> = +70°C	I <sub>D</sub>	15.2 12.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	45	A
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	1.6	A
Pulsed Source-Drain Diode Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	45	A
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	12	A
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	8	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.89	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	140	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.39	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	90	°C/W
Thermal Resistance, Junction to Case (Note 6)	Steady State	R <sub>θJC</sub>	15	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 8)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.35	—	0.95	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	16	24	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 6.5A
			18	28		
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A
<b>DYNAMIC CHARACTERISTICS</b> (Note 9)						
Input Capacitance	C <sub>iss</sub>	—	647	—	pF	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	78	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	38	—	pF	
Gate Resistance	R <sub>G</sub>	—	400	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	6.5	—	nC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6.5A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	14.8	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	1.1	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	1.7	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	98	—	ns	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 6Ω, R <sub>L</sub> = 10Ω, I <sub>D</sub> = 1A
Turn-On Rise Time	t <sub>R</sub>	—	140	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	1024	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	434	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	245	—	ns	I <sub>F</sub> = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	149	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  - I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

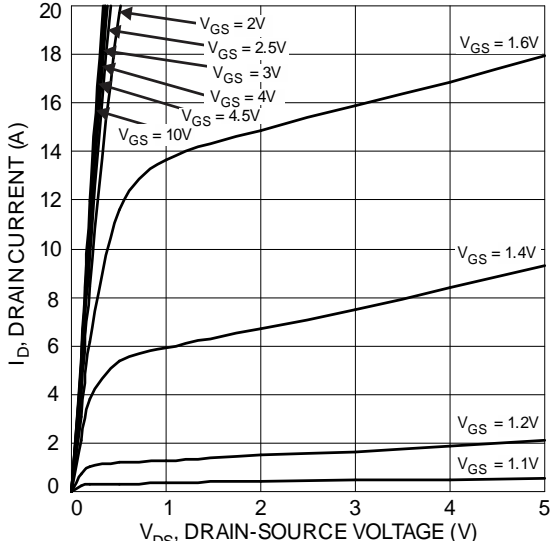


Figure 1 Typical Output Characteristic

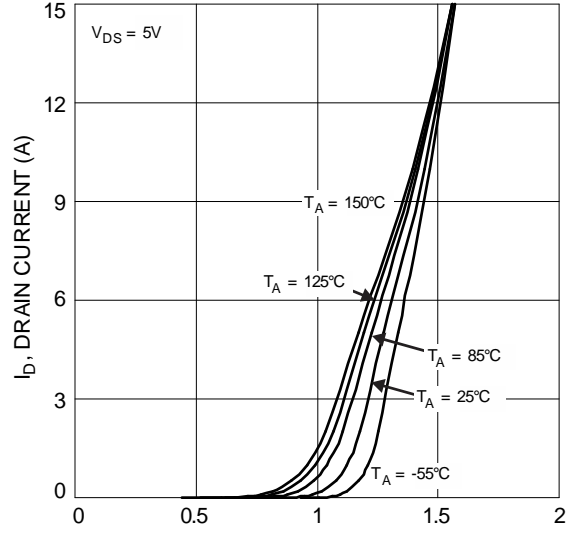


Figure 2 Typical Transfer Characteristics

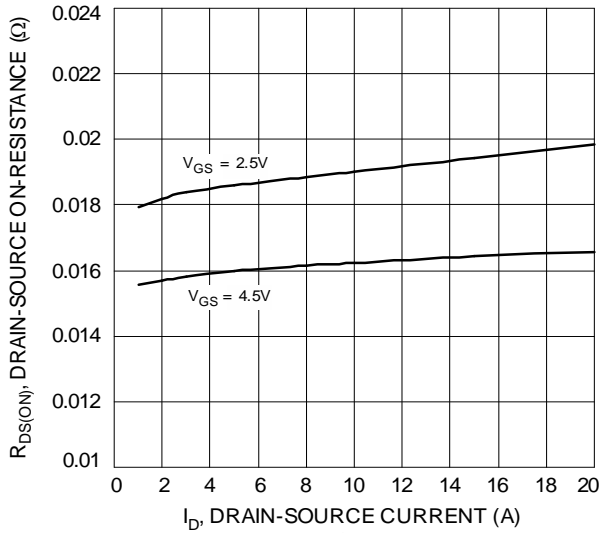


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

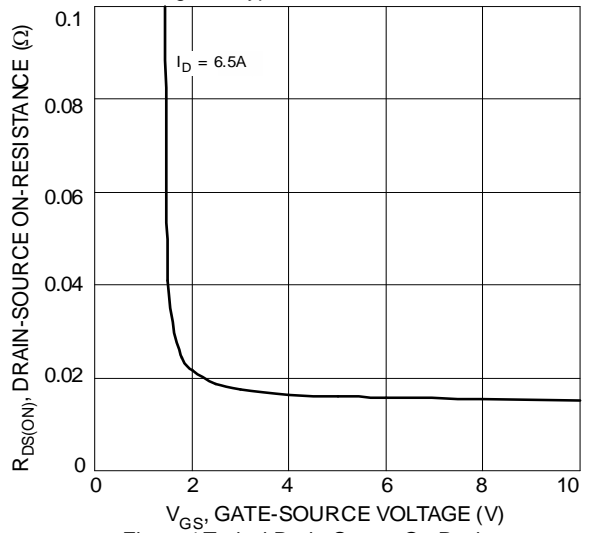


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

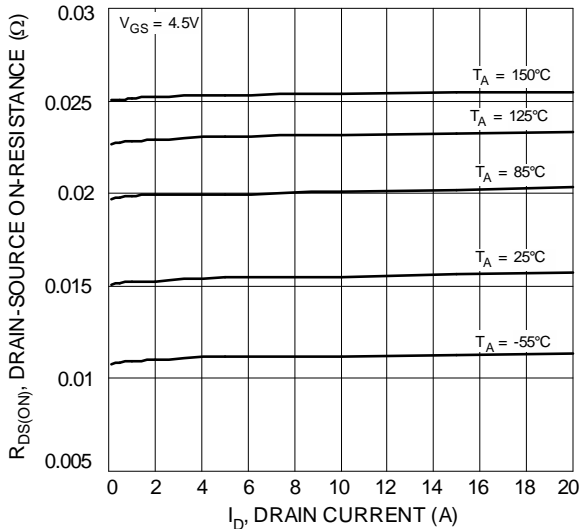


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

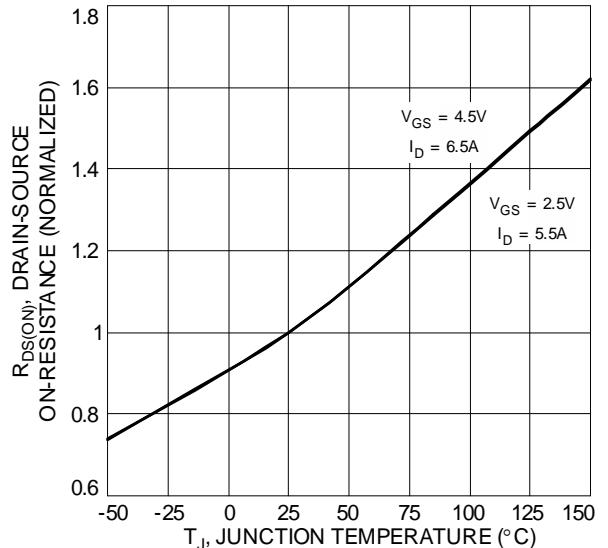


Figure 6 On-Resistance Variation with Temperature

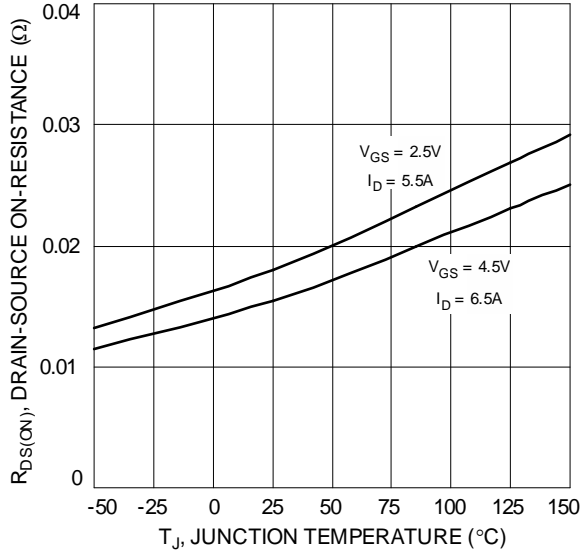


Figure 7 On-Resistance Variation with Temperature

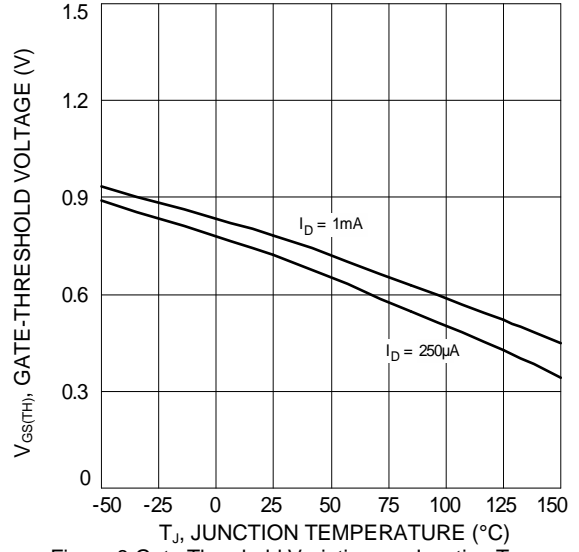


Figure 8 Gate Threshold Variation vs. Junction Temperature

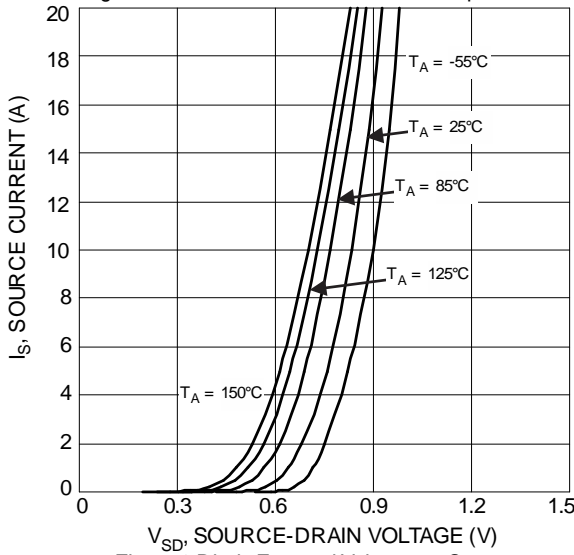


Figure 9 Diode Forward Voltage vs. Current

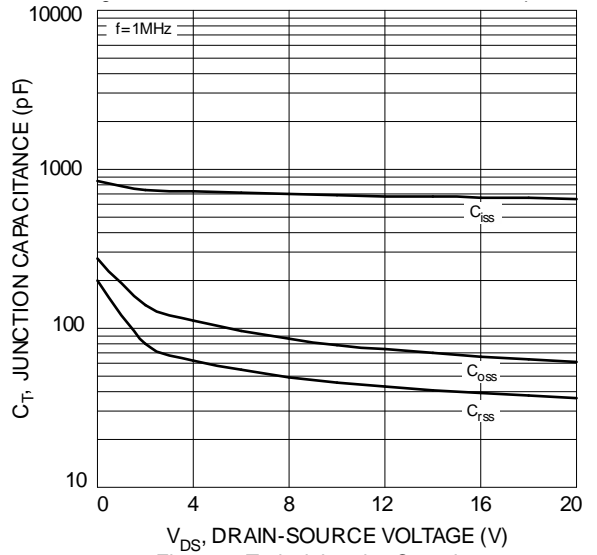


Figure 10 Typical Junction Capacitance

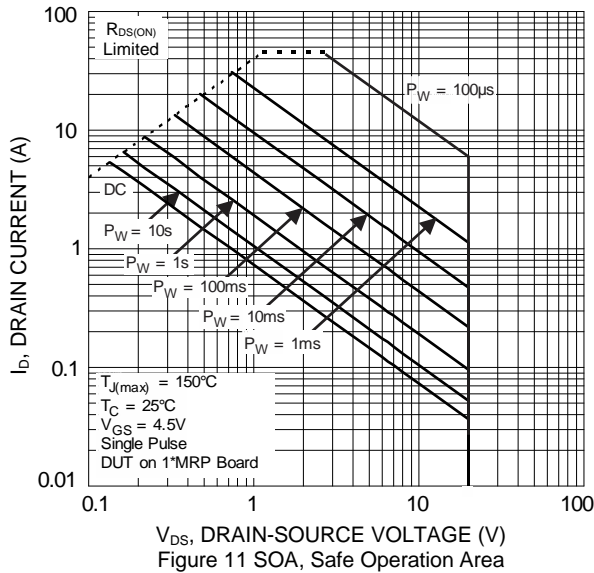


Figure 11 SOA, Safe Operation Area

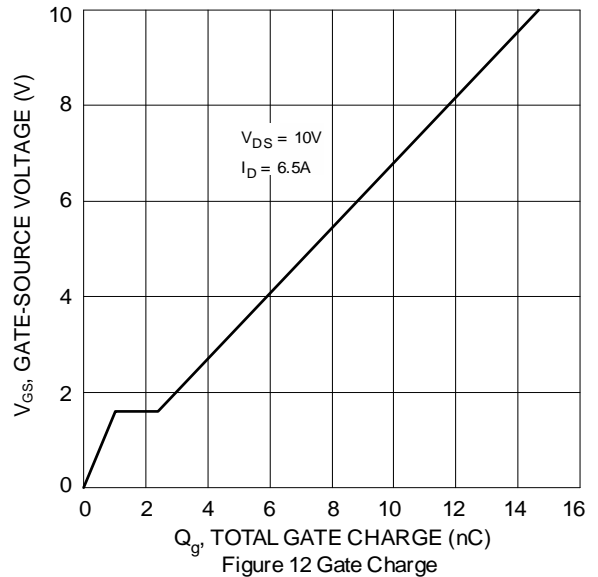
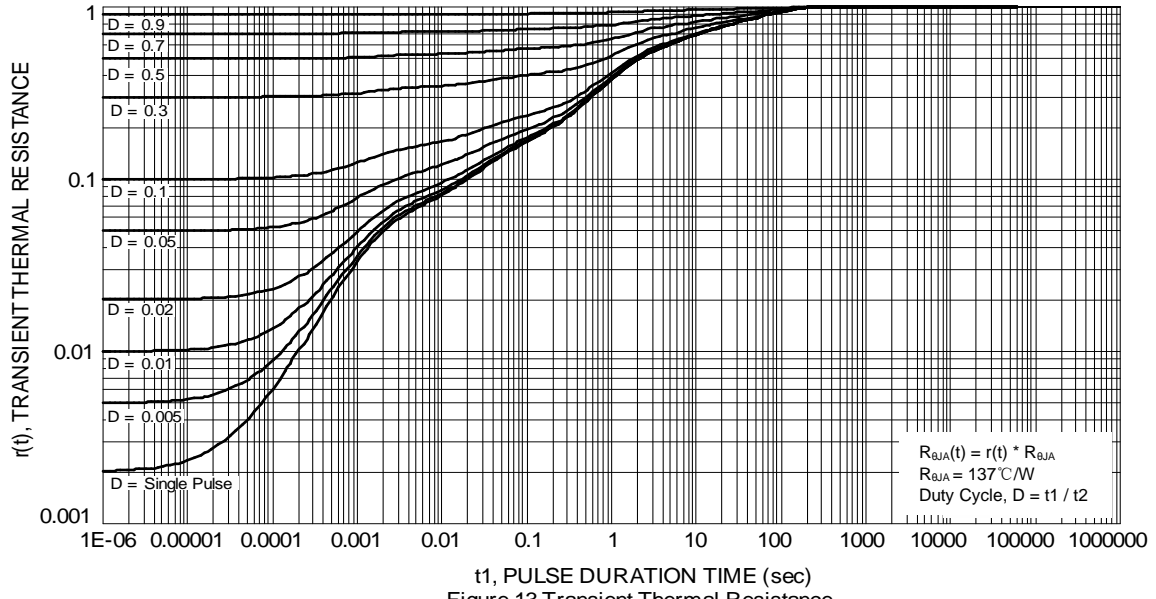


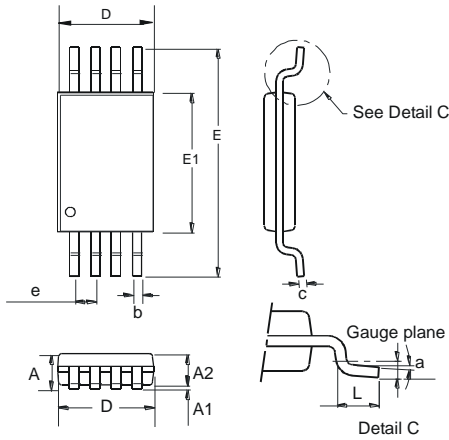
Figure 12 Gate Charge



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TSSOP-8**

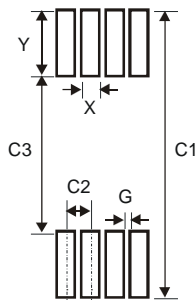


TSSOP-8			
Dim	Min	Max	Typ
a	0.09	-	-
A	-	1.20	-
A1	0.05	0.15	-
A2	0.825	1.025	0.925
b	0.19	0.30	-
c	0.09	0.20	-
D	2.90	3.10	3.025
e	-	-	0.65
E	-	-	6.40
E1	4.30	4.50	4.425
L	0.45	0.75	0.60
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**TSSOP-8**



Dimensions	Value (in mm)
X	0.45
Y	1.78
C1	7.72
C2	0.65
C3	4.16
G	0.20

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